IN THE CLAIMS:

Replace the indicated claims with:

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1. (Amended) A high frequency semiconductor integrated circuit comprising:
a main circuit having an active element and a first pad;
a circuit block of a passive element;
a second pad connected to said circuit block; and
a wire connecting said first pad to said second pad.

2. (Amended) The high frequency semiconductor integrated circuit according to claim 1, wherein said main circuit includes an input terminal and an output terminal and said active element and said first pad are located between said input terminal and said output terminal.

3. (Amended) The high frequency semiconductor integrated circuit according to claim 2, wherein said passive element has an impedance that decreases with an increase in frequency of an input signal input to said input terminal.

4. (Amended) The high frequency semiconductor integrated circuit according to claim 2, wherein said circuit block includes an interconnect connected to said second pad and wherein said wire and said interconnect have lengths totaling one-fourth of a wavelength of a high frequency signal input to said input terminal.

5. (Amended) A high frequency semiconductor integrated circuit comprising:
a main circuit having an active element and a main pad;
plural circuit blocks, each circuit block constituted of a passive element;
plural connection pads corresponding to respective plural circuit blocks; and
a wire for connecting said main pad to one of said plural connection pads.

6. (Amended) The high frequency semiconductor integrated circuit according to claim 5, wherein said main circuit includes an input terminal and an output terminal and said active element and said main pad are located between said input terminal and said output terminal.

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7. (Amended) The high frequency semiconductor integrated circuit according to claim 6, wherein said plural circuit blocks include:

a first circuit block for adjusting an impedance of said main circuit to a first impedance;

a second circuit block for adjusting the impedance of said main circuit to a second impedance; and

a third circuit block for adjusting the impedance of said main circuit to a third impedance.

8. (Amended) The high frequency semiconductor integrated circuit according to claim 7, wherein

said first circuit block is constituted of a first capacitor having a first capacitance and connected to a ground node at a first end of said first capacitor and a first connection pad at a second end of said first capacitor,

said second circuit block is constituted of a second capacitor having a second capacitance and connected to the ground node at a first end of said second capacitor and a second connection pad at a second end of said second capacitor, and

said third circuit block is constituted of a third capacitor having a third capacitance and connected to the ground node at a first end of said third capacitor and a third connection pad at a second end of said third capacitor.

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10. (Amended) The high frequency semiconductor integrated circuit according to claim 9, wherein

said first high frequency semiconductor integrated circuit comprises a main circuit having an active element and a circuit block having a passive element; and

said second high frequency semiconductor integrated circuit includes only a main circuit having an active element.

11. (Amended) The high frequency semiconductor integrated circuit according to claim 10, wherein

said second high frequency semiconductor integrated circuit includes a first main circuit having a first active element and a first pad, and

said first high frequency semiconductor integrated circuit includes:

a circuit block having a passive element;

a second pad connected to said circuit block;

a second main circuit having a third pad for connecting said first and second pads to each other, and a second active element; and

a wire for connecting said second pad to said third pad, wherein said main wire connects said first pad to said third pad.

12. (Amended) The high frequency semiconductor integrated circuit according to claim 11, wherein

said first main circuit further includes:

an interconnect connected at a first end to said first pad and at a second end to said first active element; and

an output terminal connected to said first active element, and

said second main circuit further includes:

an interconnect connected at a first end to said third pad and at a second end to said second active element; and

an input terminal connected to said second active element.

13. (Amended) The high frequency semiconductor integrated circuit according to claim 12, wherein said circuit block includes a passive element for matching an impedance of said first main circuit to an impedance of said second main circuit.

14. (Amended) The high frequency semiconductor integrated circuit according to claim 9, wherein

said first high frequency semiconductor integrated circuit includes only one main circuit having an active element, and

said second high frequency semiconductor integrated circuit includes only one circuit block having a passive element.

15. (Amended) The high frequency semiconductor integrated circuit according to claim 14, wherein

said first high frequency semiconductor integrated circuit includes a main circuit having an active element and a main pad,

said second high frequency semiconductor integrated circuit includes plural circuit blocks, each circuit block having a passive element, and

plural connection pads corresponding to respective plural circuit blocks, wherein said main wire connects said main pad to one of said plural connection pads.

IN THE ABSTRACT:

Replace the abstract with:

ABSTRACT OF THE DISCLOSURE

A high frequency semiconductor integrated circuit includes a main circuit, a circuit block, a pad, and a wire. The main circuit includes an input terminal, a transistor, transmission lines, a pad, and an output terminal. The circuit block includes a passive circuit and a capacitor. The pad is disposed close to the circuit block. The wire connects the pad to the pad included in the main circuit. In the high frequency semiconductor integrated circuit, the main circuit outputs an input signal input at the input terminal from the output terminal through the transistor, the transmission line, the pad, and another transmission line. As a result, the high frequency semiconductor integrated circuit can realize various performances and can be used in many applications.